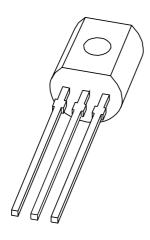
# DISCRETE SEMICONDUCTORS

# DATA SHEET



# PH2369 NPN switching transistor

Product data sheet Supersedes data of 1999 Apr 27 2004 Oct 11



# NPN switching transistor

PH2369

#### **FEATURES**

- Low current (max. 200 mA)
- Low voltage (max. 15 V).

#### **APPLICATIONS**

• High-speed switching.

#### **DESCRIPTION**

NPN switching transistor in a TO-92; SOT54 plastic package.

#### **PINNING**

PIN	DESCRIPTION
1	emitter
2	base
3	collector

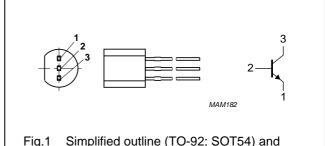


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE	
TIPE NOWIBER	NAME DESCRIPTIO		VERSION
PH2369	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	40	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	15	٧
V <sub>EBO</sub>	emitter-base voltage	open collector	_	4.5	V
I <sub>C</sub>	collector current (DC)		_	200	mA
I <sub>CM</sub>	peak collector current		_	300	mA
I <sub>BM</sub>	peak base current		_	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	-	500	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	250	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

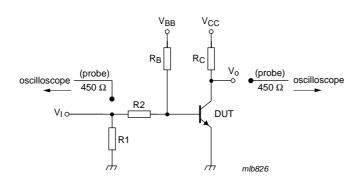
#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 20 V; I <sub>E</sub> = 0 A	_	400	nA
		V <sub>CB</sub> = 20 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 125 °C	_	30	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0 A	_	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1 V; I <sub>C</sub> = 10 mA	40	120	
		$V_{CE} = 1 \text{ V; } I_{C} = 10 \text{ mA; } T_{amb} = -55 ^{\circ}\text{C}$	20	_	
		V <sub>CE</sub> = 2 V; I <sub>C</sub> = 100 mA	20	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	_	250	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	700	850	mV
C <sub>c</sub>	collector capacitance	$V_{CB} = 5 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$	_	4	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 1 \text{ V}; I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}$	_	4.5	pF
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 10 mA; f = 100 MHz	500	_	MHz
Switching t	imes (between 10 % and 90 % leve	ls)			
t <sub>on</sub>	turn-on time	$I_{Con} = 10 \text{ mA}$ ; $I_{Bon} = 3 \text{ mA}$ ; $I_{Boff} = -1.5 \text{ mA}$ ;	_	10	ns
t <sub>d</sub>	delay time	see Fig.2 test conditions A	_	4	ns
t <sub>r</sub>	rise time		_	6	ns
t <sub>off</sub>	turn-off time			20	ns
t <sub>s</sub>	storage time		_	10	ns
t <sub>f</sub>	fall time		_	10	ns
t <sub>on</sub>	turn-on time	$I_{Con} = 100 \text{ mA}$ ; $I_{Bon} = 40 \text{ mA}$ ; $I_{Boff} = -20 \text{ mA}$ ;	-	13	ns
t <sub>off</sub>	turn-off time	see Fig.2 test conditions B		35	ns

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#### Test conditions A.

$$\begin{split} &V_i = 0.5 \text{ to } 4.2 \text{ V}; \text{ T} = 500 \text{ } \mu\text{s}; \text{ } t_p = 10 \text{ } \mu\text{s}; \text{ } t_f = t_f \leq 3 \text{ ns.} \\ &R1 = 56 \text{ } \Omega; \text{ } R2 = 1 \text{ } k\Omega; \text{ } R_B = 1 \text{ } k\Omega; \text{ } R_C = 270 \text{ } \Omega. \\ &V_{BB} = 0.2 \text{ V}; \text{ } V_{CC} = 2.7 \text{ V}. \\ &Oscilloscope: input impedance \text{ } Z_i = 50 \text{ } \Omega. \end{split}$$

#### Test conditions B.

$$\begin{split} &V_i=0.5~to~4.52~V;~T=200~\mu s;~t_p=10~\mu s;~t_f=t_f\leq 3~ns.\\ &R1=100~\Omega;~R2=68~\Omega;~R_B=390~\Omega;~R_C=47~\Omega.\\ &V_{BB}=-3~V;~V_{CC}=4.6~V.\\ &Oscilloscope:~input~impedance~Z_i=50~\Omega. \end{split}$$

Fig.2 Test circuit for switching times.

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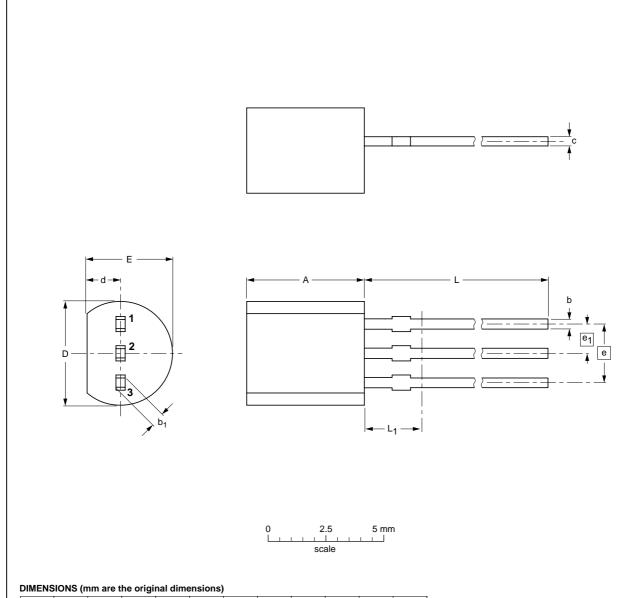
# NPN switching transistor

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#### **PACKAGE OUTLINE**

#### Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	A	b	b <sub>1</sub>	С	D	d	E	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	

#### Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			<del>-04-06-28</del> 04-11-16

## NPN switching transistor

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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#### **Contact information**

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